## MC74HCT241A

## Octal 3-State Noninverting Buffer/Line Driver/ Line Receiver with LSTTL-Compatible Inputs

## High-Performance Silicon-Gate CMOS

The MC74HCT241A is identical in pinout to the LS241. This device may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT241A is an octal noninverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has non-inverted outputs and two output enables. Enable A is active-low and Enable B is active-high.

The HCT241A is similar in function to the HCT244. See also HCT240.

## Features

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: $1.0 \mu \mathrm{~A}$
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 118 FETs or 29.5 Equivalent Gates
- $\mathrm{Pb}-$ Free Packages are Available*

[^0]


| PIN ASSIGNMENT |  |  |  |
| :---: | :---: | :---: | :---: |
| ENABLEA | $1 \bullet$ | 20 | $\mathrm{V}_{\mathrm{CC}}$ |
| A1 | 2 | 19 | ENABLE B |
| YB4 ${ }^{\text {¢ }}$ | 3 | 18 | Y Y 1 |
| A2 | 4 | 17 | ] B4 |
| YB3 [ | 5 | 16 | YA2 |
| A3 | 6 | 15 | B3 |
| YB2 ${ }^{\text {C }}$ | 7 | 14 | Y Y 3 |
| A4 | 8 | 13 | B2 |
| YB1 ${ }^{\text {C }}$ | 9 | 12 | YA4 |
| GND | 10 | 11 | ] B1 |

## FUNCTION TABLE

| Inputs |  | Output |
| :---: | :---: | :---: |
| Enable A | A | YA |
| L | L | L |
| L | H | H |
| H | X | Z |


| Inputs |  | Output |
| :---: | :---: | :---: |
| Enable B | B | YB |
| H | L | L |
| H | H | H |
| L | X | Z |

$\mathrm{Z}=$ high impedance
X = don't care

MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\text {in }}$ | DC Input Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{~V}_{\text {out }}$ | DC Output Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{I}_{\text {in }}$ | DC Input Current, per Pin | $\pm 20$ | mA |
| $\mathrm{I}_{\text {out }}$ | DC Output Current, per Pin | $\pm 35$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ | DC Supply Current, $\mathrm{V}_{\mathrm{CC}}$ and GND Pins | $\pm 75$ | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air, Plastic or Ceramic DIPt |  |  |
| SOIC Packaget |  |  |  |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, $\mathrm{V}_{\text {in }}$ and $V_{\text {out }}$ should be constrained to the range $G N D \leq\left(\mathrm{V}_{\text {in }}\right.$ or $\left.\mathrm{V}_{\text {out }}\right) \leq \mathrm{V}_{\mathrm{Cc}}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $\mathrm{V}_{\mathrm{CC}}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
$\dagger$ Derating - Plastic DIP: - $10 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
Ceramic DIP: $-10 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $100^{\circ}$ to $125^{\circ} \mathrm{C}$
SOIC Package: $-7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | 4.5 | 5.5 | V |
| $\mathrm{~V}_{\mathrm{in}}, \mathrm{V}_{\text {out }}$ | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | $\mathrm{~V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature, All Package Types | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time (Figure 1) | 0 | 500 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | $\mathrm{v}_{\mathrm{VC}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage | $\begin{aligned} & \mathrm{V}_{\text {out }}=0.1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \mid l_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 2 \\ & 2 \end{aligned}$ | $\begin{aligned} & 2 \\ & 2 \end{aligned}$ | $\begin{aligned} & 2 \\ & 2 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{IL}}$ | Maximum Low-Level Input Voltage | $\begin{aligned} & \mathrm{V}_{\text {out }}=0.1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \mid l_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline 0.8 \\ & 0.8 \end{aligned}$ | $\begin{aligned} & \hline 0.8 \\ & 0.8 \end{aligned}$ | $\begin{aligned} & \hline 08 \\ & 0.8 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage | $\begin{aligned} & \begin{array}{l} \mathrm{V}_{\text {in }} \\ \mid \mathrm{V}_{\text {IH }} \text { or } \mathrm{V}_{\mathrm{IL}} \end{array} \end{aligned}$ | $\begin{aligned} & \hline 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | V |
|  |  | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mid l_{\text {out }} \leq 6 \mathrm{~mA} \end{aligned}$ | 4.5 | 3.98 | 3.84 | 3.7 |  |
| V OL | Maximum Low-Level Output Voltage | $\begin{aligned} & \begin{array}{l} \mathrm{V}_{\text {in }} \\ \mid \mathrm{V}_{\text {IH }} \text { or } \mathrm{V}_{\mathrm{IL}} \end{array} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \end{aligned}$ | V |
|  |  | $\begin{aligned} & \mathrm{V}_{\text {in }} \mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mid l_{\text {out }} \leq 6 \mathrm{~mA} \end{aligned}$ | 4.5 | 0.26 | 0.33 | 0.4 |  |
| $\mathrm{l}_{\text {in }}$ | Maximum Input Leakage Current | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {CC }}$ or GND | 5.5 | $\pm 0.1$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| $\mathrm{l}_{\text {OZ }}$ | Maximum Three-State Leakage Current | Output in High-Impedance State $\begin{aligned} & V_{\text {in }}=V_{\text {IL }} \text { or } V_{\text {IH }} \\ & V_{\text {out }}=V_{C C} \text { or } G N D \end{aligned}$ | 5.5 | $\pm 0.5$ | $\pm 5.0$ | $\pm 10$ | $\mu \mathrm{A}$ |
| Icc | Maximum Quiescent Supply Current (per Package) | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ & \mathrm{I}_{\text {out }}=0 \mu \mathrm{~A} \end{aligned}$ | 5.5 | 4 | 40 | 160 | $\mu \mathrm{A}$ |
| $\Delta_{\text {l }} \mathrm{CC}$ | Additional Quiescent Supply Current | $\begin{aligned} & \mathrm{V}_{\text {in }}=2.4 \mathrm{~V} \text {, Any One Input } \\ & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND, Other Inputs } \\ & \mathrm{I}_{\text {out }}=0 \mu \mathrm{~A} \end{aligned}$ | 5.5 | $\geq-55^{\circ} \mathrm{C}$ | $25^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$ |  | mA |
|  |  |  |  | 2.9 | 2.4 |  |  |

1. Total Supply Current $=\mathrm{I}_{\mathrm{CC}}+\Sigma \Delta \mathrm{I}_{\mathrm{CC}}$.

AC ELECTRICAL CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 10 \%, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}\right.$, Input $\left.\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6 \mathrm{~ns}\right)$

| Symbol | Parameter | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\begin{aligned} & \mathrm{t}_{\text {PLH }}, \\ & \mathrm{t}_{\text {PHL }} \end{aligned}$ | Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3) | 23 | 29 | 35 | ns |
| $\begin{aligned} & \text { tpLZ, } \\ & \mathrm{t}_{\mathrm{PH}} \end{aligned}$ | Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4) | 30 | 38 | 45 | ns |
| $\begin{aligned} & \text { tpZL, } \\ & \mathrm{t}_{\text {PZH }} \end{aligned}$ | Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4) | 26 | 33 | 39 | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{TLLH}}, \\ & \mathrm{t}_{\mathrm{TH}}, \end{aligned}$ | Maximum Output Transition Time, Any Output (Figures 1 and 3) | 12 | 15 | 18 | ns |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance | 10 | 10 | 10 | pF |
| $\mathrm{C}_{\text {out }}$ | Maximum Three-State Output Capacitance (Output in High-Impedance State) | 15 | 15 | 15 | pF |


|  |  | Typical @ $\mathbf{2 5}{ }^{\circ} \mathbf{C}, \mathbf{V}_{\mathbf{C C}}=\mathbf{5 . 0} \mathbf{V}$ |  |
| :---: | :---: | :---: | :---: |
| $\mathrm{C}_{\text {PD }}$ | Power Dissipation Capacitance (Per Enabled Output)* | 55 | pF |

*Used to determine the no-load dynamic power consumption: $P_{D}=C_{P D} V_{C C}{ }^{2}+I_{C C} V_{C C}$.

## SWITCHING WAVEFORMS



Figure 1.
Figure 2.

*Includes all probe and jig capacitance
Figure 3. Test Circuit

*Includes all probe and jig capacitance
Figure 4. Test Circuit

MC74HCT241A

LOGIC DETAIL


## ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| MC74HCT241ANG | PDIP－20 <br> （Pb－Free） | 18 Units／Rail |
| MC74HCT241ADWG | SOIC－20 <br> （Pb－Free） | 38 Units／Rail |
| MC74HCT241ADWR2G | SOIC－20 <br> （Pb－Free） | $1000 /$ Tape \＆Reel |
| MC74HCT241ADTG | TSSOP－20＊ | 75 Units／Rail |
| MC74HCT241ADTR2G | TSSOP－20＊ | 2500 ／Tape \＆Reel |

$\dagger$ For information on tape and reel specifications，including part orientation and tape sizes，please refer to our Tape and Reel Packaging Specifications Brochure，BRD8011／D．
＊These packages are inherently $\mathrm{Pb}-$ Free．

## MARKING DIAGRAMS

## PDIP－20



SOIC－20W
20日月日日月日月月日


1 $\mathrm{\theta}$ 昭

TSSOP－20
20 AHBABHARA
HCT
241A ALYW•
0


A＝Assembly Location
WL，L＝Wafer Lot
YY，$Y=$ Year
WW，W＝Work Week
G or $\quad=\mathrm{Pb}-$ Free Package
（Note：Microdot may be in either location）


SCALE 1:1


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES

PER ASME Y14.5M, 1994
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION PROTRUSION. ALLOWABLE PROTRUSION
SHALL BE 0.13 TOTAL IN EXCESS OF B SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| DIM | MILLIMETERS |  |
| :---: | ---: | ---: |
|  | MIN | MAX |
| A | 2.35 | 2.65 |
| A1 | 0.10 | 0.25 |
| b | 0.35 | 0.49 |
| $\mathbf{c}$ | 0.23 | 0.32 |
| D | 12.65 | 12.95 |
| E | 7.40 | 7.60 |
| e | 1.27 BSC |  |
| H | 10.05 | 10.55 |
| $\mathbf{h}$ | 0.25 | 0.75 |
| L | 0.50 | 0.90 |
| $\boldsymbol{\theta}$ | $0^{\circ}$ | $7^{\circ}$ |

GENERIC
MARKING DIAGRAM*


| XXXXX | $=$ Specific Device Code |
| :--- | :--- |
| A | $=$ Assembly Location |
| WL | $=$ Wafer Lot |
| YY | $=$ Year |
| WW | $=$ Work Week |
| G | $=$ Pb-Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SOIC-20 WB | PAGE 1 OF 1 |

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TSSOP-20 WB
CASE 948E
ISSUE D
DATE 17 FEB 2016

SCALE 2:1


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
CONTROLLING DIMENSION: MILLIMETER
2. DIMENSION A DOES NOT INCLUDE MOLD

FLASH, PROTRUSIONS OR GATE BURRS.
FLASH, PROTRUSIONS OR GATE BURRS.
MOLD FLASH OR GATE BURRS SHALL NO
EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE

INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED $0.25(0.010)$ PER SIDE
5. DIMENSION K DOES NOT INCLUDE

DAMBAR PROTRUSION. ALLOWABLE
DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |
| A | 6.40 | 6.60 | 0.252 | 0.260 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC |  | 0.026 BSC |  |
| H | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 BSC |  |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |

GENERIC MARKING DIAGRAM* НРННННННН

|  | XXXX |
| :---: | :---: |
|  | XXXX |
|  | ALYW. |
| $\bigcirc$ | - |

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.
DIMENSIONS: MILLIMETERS

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP-20 WB | PAGE 1 OF 1 |

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[^0]:    *For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

